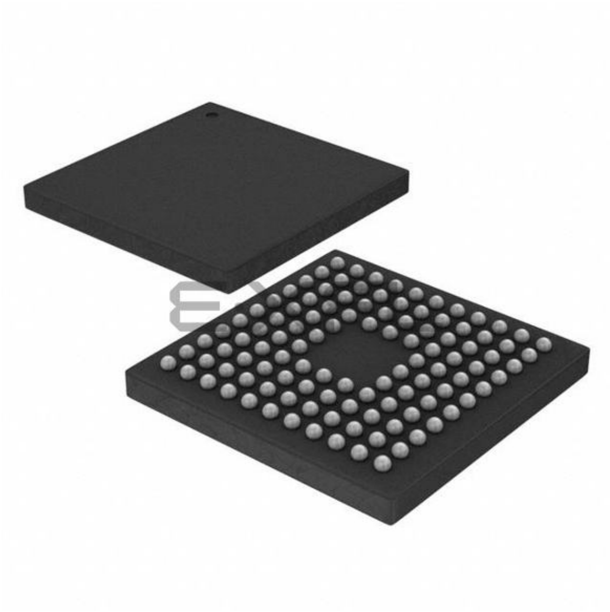

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	90
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	112-LFBGA
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg890f64-bga112

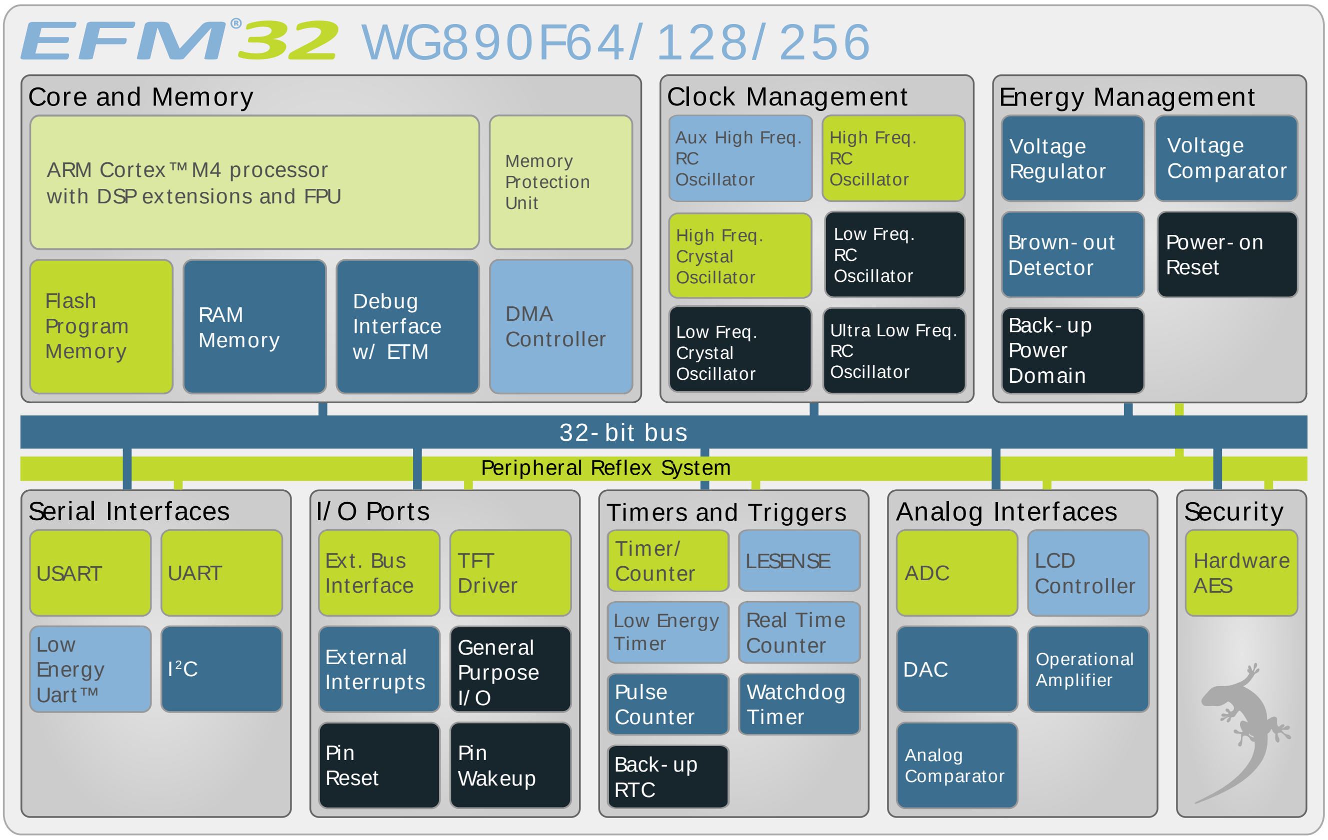
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world’s most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M4, with DSP instruction support and floating-point unit, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32WG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32WG890 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32WG Reference Manual*.

A block diagram of the EFM32WG890 is shown in Figure 2.1 (p. 3) .

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M4 Core

The ARM Cortex-M4 includes a 32-bit RISC processor, with DSP instruction support and floating-point unit, which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Memory Protection Unit with support for up to 8 memory segments is included, as well as a Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep. The EFM32 implementation of the Cortex-M4 is described in detail in *ARM Cortex-M4 Devices Generic User Guide*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface and an Embedded Trace Module (ETM) for data/instruction tracing. In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

2.1.19 Backup Real Time Counter (BURTC)

The Backup Real Time Counter (BURTC) contains a 32-bit counter and is clocked either by a 32.768 kHz crystal oscillator, a 32.768 kHz RC oscillator or a 1 kHz ULFRCO. The BURTC is available in all Energy Modes and it can also run in backup mode, making it operational even if the main power should drain out.

2.1.20 Low Energy Timer (LETIMER)

The unique LETIMER^{TM}, the Low Energy Timer, is a 16-bit timer that is available in energy mode EM2 in addition to EM1 and EM0. Because of this, it can be used for timing and output generation when most of the device is powered down, allowing simple tasks to be performed while the power consumption of the system is kept at an absolute minimum. The LETIMER can be used to output a variety of waveforms with minimal software intervention. It is also connected to the Real Time Counter (RTC), and can be configured to start counting on compare matches from the RTC.

2.1.21 Pulse Counter (PCNT)

The Pulse Counter (PCNT) can be used for counting pulses on a single input or to decode quadrature encoded inputs. It runs off either the internal LFACLK or the PCNTn_S0IN pin as external clock source. The module may operate in energy mode EM0 – EM3.

2.1.22 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.23 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.24 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 8 external pins and 6 internal signals.

2.1.25 Digital to Analog Converter (DAC)

The Digital to Analog Converter (DAC) can convert a digital value to an analog output voltage. The DAC is fully differential rail-to-rail, with 12-bit resolution. It has two single ended output buffers which can be combined into one differential output. The DAC may be used for a number of different applications such as sensor interfaces or sound output.

2.1.26 Operational Amplifier (OPAMP)

The EFM32WG890 features 3 Operational Amplifiers. The Operational Amplifier is a versatile general purpose amplifier with rail-to-rail differential input and rail-to-rail single ended output. The input can be set to pin, DAC or OPAMP, whereas the output can be pin, OPAMP or ADC. The current is programmable and the OPAMP has various internal configurations such as unity gain, programmable gain using internal resistors etc.

2.1.27 Low Energy Sensor Interface (LESENSE)

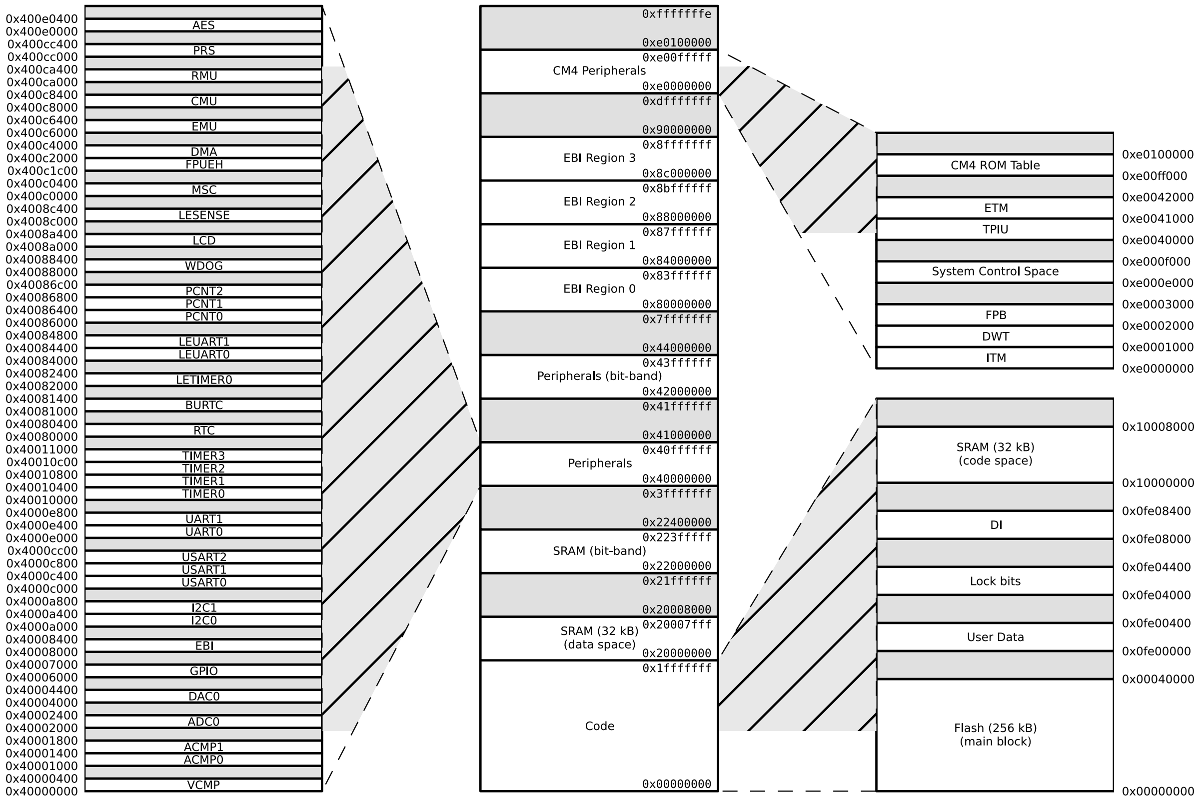
The Low Energy Sensor Interface (LESENSE^{TM}), is a highly configurable sensor interface with support for up to 16 individually configurable sensors. By controlling the analog comparators and DAC, LESENSE

Module	Configuration	Pin Connections
CMU	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA
PRS	Full configuration	NA
EBI	Full configuration	EBI_A[27:0], EBI_AD[15:0], EBI_ARDY, EBI_ALE, EBI_BL[1:0], EBI_CS[3:0], EBI_CSTFT, EBI_DCLK, EBI_DTEN, EBI_HSNC, EBI_NANDREn, EBI_NANDWEn, EBI_REn, EBI_VSNC, EBI_WEn
I2C0	Full configuration	I2C0_SDA, I2C0_SCL
I2C1	Full configuration	I2C1_SDA, I2C1_SCL
USART0	Full configuration with IrDA	US0_TX, US0_RX. US0_CLK, US0_CS
USART1	Full configuration with I2S	US1_TX, US1_RX, US1_CLK, US1_CS
USART2	Full configuration with I2S	US2_TX, US2_RX, US2_CLK, US2_CS
UART0	Full configuration	U0_TX, U0_RX
UART1	Full configuration	U1_TX, U1_RX
LEUART0	Full configuration	LEU0_TX, LEU0_RX
LEUART1	Full configuration	LEU1_TX, LEU1_RX
TIMER0	Full configuration with DTI	TIM0_CC[2:0], TIM0_CDTI[2:0]
TIMER1	Full configuration	TIM1_CC[2:0]
TIMER2	Full configuration	TIM2_CC[2:0]
TIMER3	Full configuration	TIM3_CC[2:0]
RTC	Full configuration	NA
BURTC	Full configuration	NA
LETIMER0	Full configuration	LET0_O[1:0]
PCNT0	Full configuration, 16-bit count register	PCNT0_S[1:0]
PCNT1	Full configuration, 8-bit count register	PCNT1_S[1:0]
PCNT2	Full configuration, 8-bit count register	PCNT2_S[1:0]
ACMP0	Full configuration	ACMP0_CH[7:0], ACMP0_O
ACMP1	Full configuration	ACMP1_CH[7:0], ACMP1_O
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:0]
DAC0	Full configuration	DAC0_OUT[1:0], DAC0_OUTxALT
OPAMP	Full configuration	Outputs: OPAMP_OUTx, OPAMP_OUTxALT, Inputs: OPAMP_Px, OPAMP_Nx
AES	Full configuration	NA
GPIO	90 pins	Available pins are shown in Table 4.3 (p. 70)
LCD	Full configuration	LCD_SEG[35:0], LCD_COM[7:0], LCD_BCAP_P, LCD_BCAP_N, LCD_BEXT

2.3 Memory Map

The *EFM32WG890* memory map is shown in Figure 2.2 (p. 9), with RAM and Flash sizes for the largest memory configuration.

Figure 2.2. EFM32WG890 Memory Map with largest RAM and Flash sizes



3.8 General Purpose Input Output

Table 3.8. GPIO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IOIL}	Input low voltage				$0.30V_{DD}$	V
V_{IOIH}	Input high voltage		$0.70V_{DD}$			V
V_{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.80V_{DD}$		V
		Sourcing 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.90V_{DD}$		V
		Sourcing 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.85V_{DD}$		V
		Sourcing 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.90V_{DD}$		V
		Sourcing 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.75V_{DD}$			V
		Sourcing 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.85V_{DD}$			V
		Sourcing 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.60V_{DD}$			V
		Sourcing 20 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.80V_{DD}$			V
V_{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.20V_{DD}$		V
		Sinking 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.10V_{DD}$		V
		Sinking 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.10V_{DD}$		V
		Sinking 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.05V_{DD}$		V
		Sinking 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.30V_{DD}$	V
		Sinking 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.20V_{DD}$	V
		Sinking 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			$0.35V_{DD}$	V

3.9 Oscillators

3.9.1 LFXO

Table 3.9. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		X[1]		25	pF
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L=10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L=10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

[1] See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in energyAware Designer in Simplicity Studio

For safe startup of a given crystal, the energyAware Designer in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

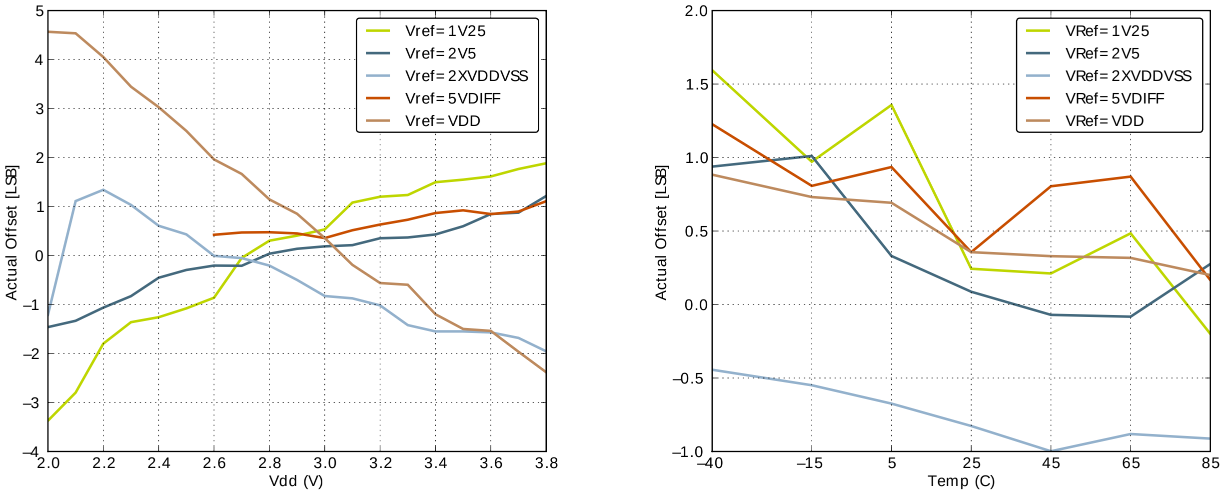
3.9.2 HFXO

Table 3.10. HFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported nominal crystal Frequency		4		48	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 48 MHz			50	Ohm
		Crystal frequency 32 MHz		30	60	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L=20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		µA
		32 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		µA
t_{HFXO}	Startup time	32 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		400		µs

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		64		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		66		dB
		1 MSamples/s, 12 bit, differential, 2xV_{DD} reference		68		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		61		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		65		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		66		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	62	66		dB
		200 kSamples/s, 12 bit, differential, 2xV_{DD} reference		69		dB
$SFDR_{ADC}$	Spurious-Free Dynamic Range (SFDR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		64		dBc
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		76		dBc
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		73		dBc
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		66		dBc
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		77		dBc
		1 MSamples/s, 12 bit, differential, V_{DD} reference		76		dBc
		1 MSamples/s, 12 bit, differential, 2xV_{DD} reference		75		dBc
		1 MSamples/s, 12 bit, differential, 5V reference		69		dBc
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		76		dBc

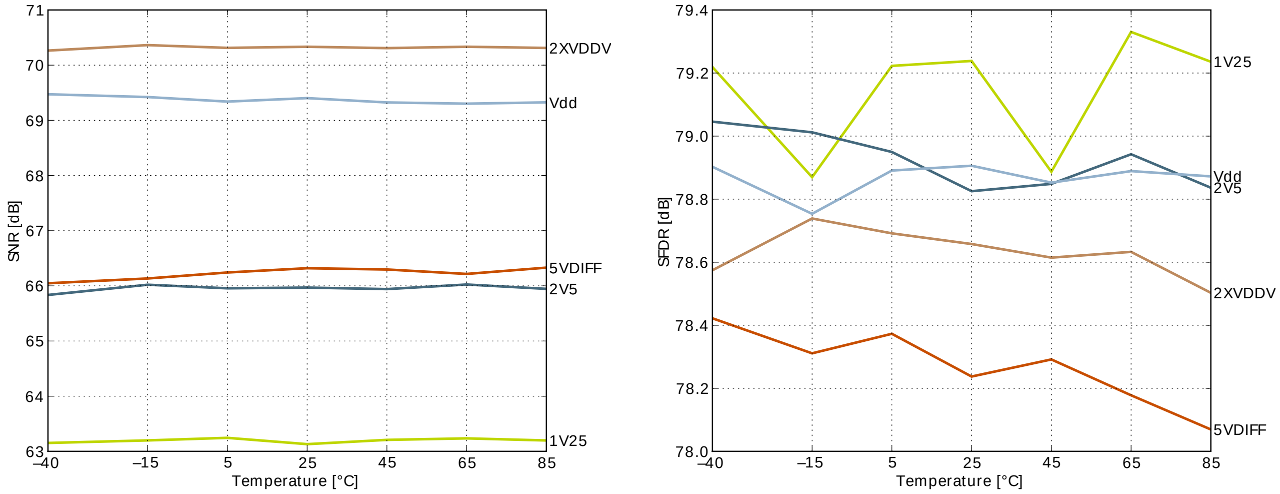
Figure 3.29. ADC Absolute Offset, Common Mode = Vdd /2



Offset vs Supply Voltage, Temp = 25°C

Offset vs Temperature, Vdd = 3V

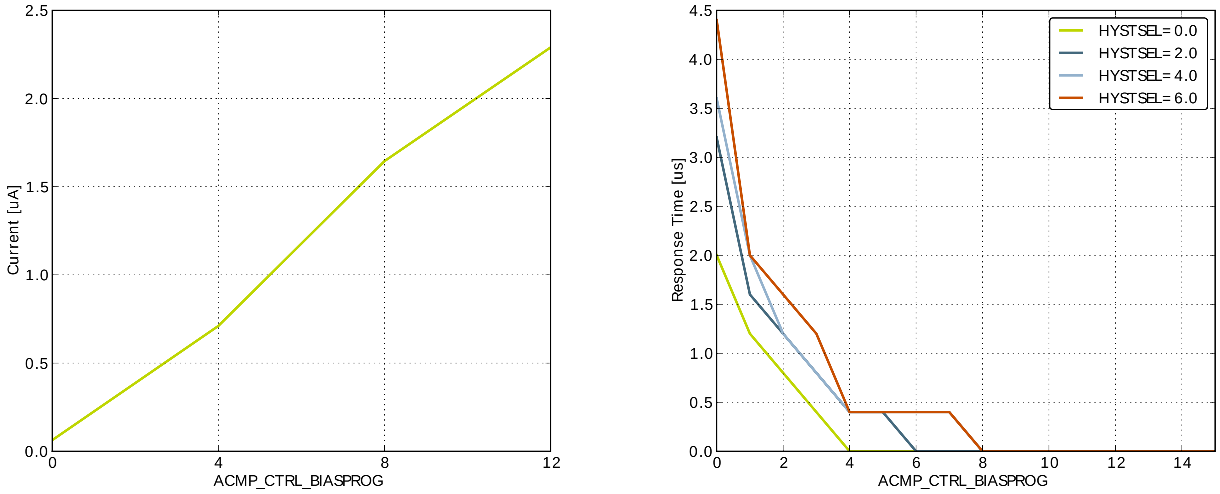
Figure 3.30. ADC Dynamic Performance vs Temperature for all ADC References, Vdd = 3V



Signal to Noise Ratio (SNR)

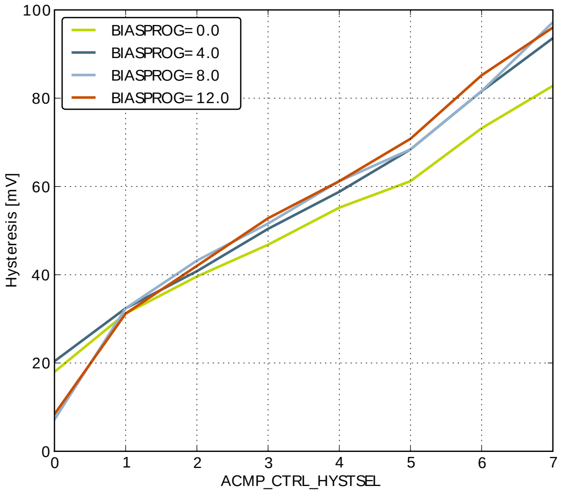
Spurious-Free Dynamic Range (SFDR)

Figure 3.37. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1



Current consumption, HYSTSEL = 4

Response time



Hysteresis

3.14 Voltage Comparator (VCMP)

Table 3.19. VCMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{VCMPIN}	Input voltage range			V_{DD}		V
V_{VCMPCM}	VCMP Common Mode voltage range			V_{DD}		V
I_{VCMP}	Active current	BIASPROG=0b0000 and HALFBIAS=1 in VCMPn_CTRL register		0.3	0.6	µA
		BIASPROG=0b1111 and HALFBIAS=0 in VCMPn_CTRL register. LPREF=0.		22	35	µA
$t_{VCMPREF}$	Startup time reference generator	NORMAL		10		µs
$V_{VCMPOFFSET}$	Offset voltage	Single ended		10		mV
		Differential		10		mV
$V_{VCMPHYST}$	VCMP hysteresis			61	210	mV
$t_{VCMPSTART}$	Startup time				10	µs

The V_{DD} trigger level can be configured by setting the TRIGLEVEL field of the VCMP_CTRL register in accordance with the following equation:

VCMP Trigger Level as a Function of Level Setting

$$V_{DD\ Trigger\ Level}=1.667V+0.034\times TRIGLEVEL \tag{3.2}$$

3.15 EBI

Figure 3.38. EBI Write Enable Timing

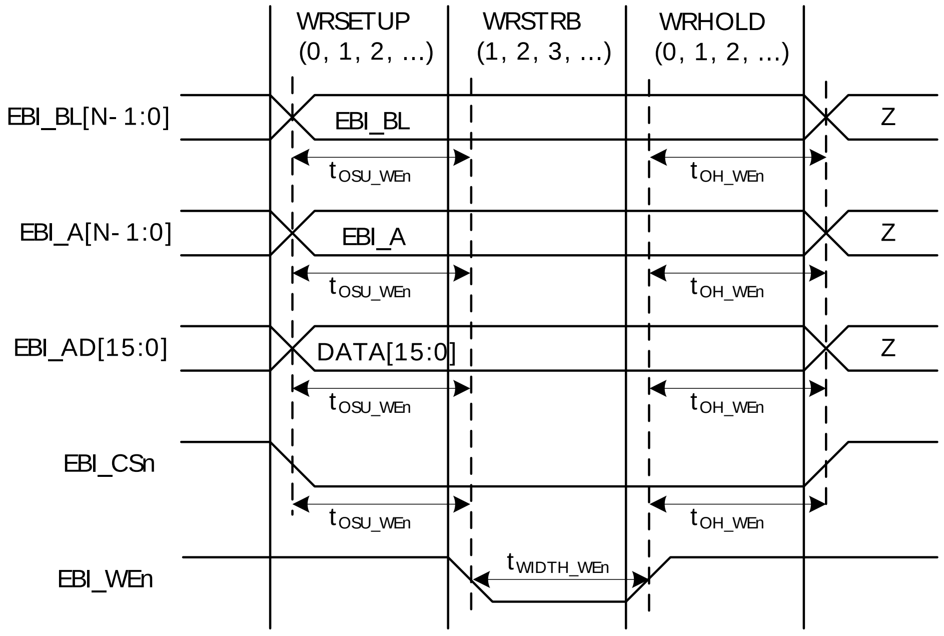


Figure 3.40. EBI Read Enable Related Output Timing

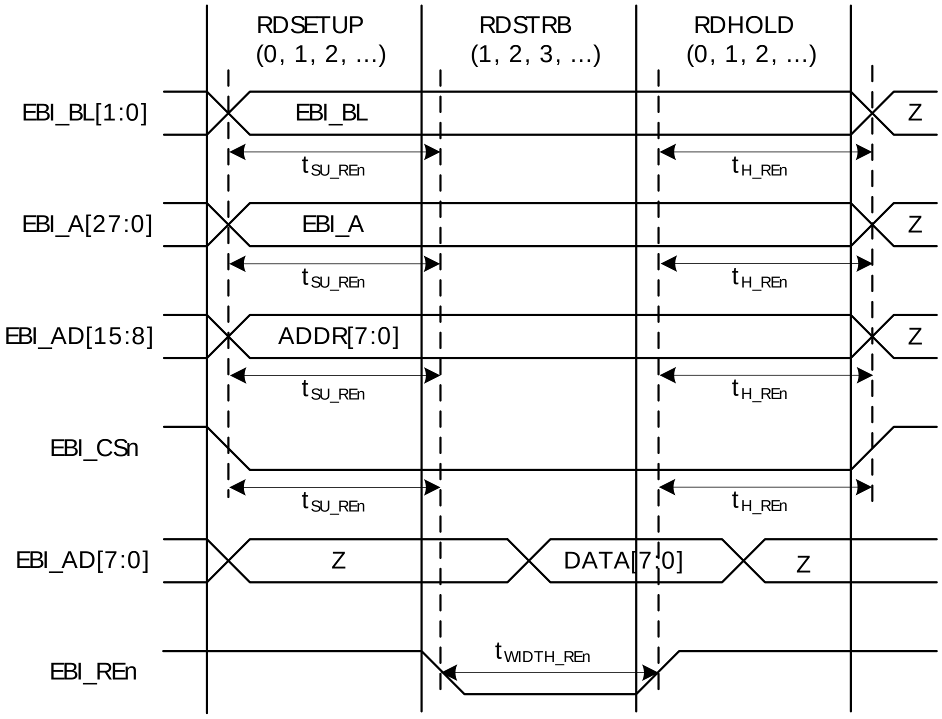


Table 3.22. EBI Read Enable Related Output Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{OH_REn} [1 2 3 4]	Output hold time, from trailing EBI_REn/ EBI_NANDREn edge to EBI_AD, EBI_A, EBI_CSn, EBI_BLn invalid	-10.00 + (RDHOLD * $t_{HFCORECLK}$)			ns
t_{OSU_REn} [1 2 3 4 5]	Output setup time, from EBI_AD, EBI_A, EBI_CSn, EBI_BLn valid to leading EBI_REn/EBI_NANDREn edge	-10.00 + (RDSETUP * $t_{HFCORECLK}$)			ns
t_{WIDTH_REn} [1 2 3 4 5 6]	EBI_REn pulse width	-9.00 + ((RDSTRB+1) * $t_{HFCORECLK}$)			ns

[1] Applies for all addressing modes (figure only shows D8A8. Output timing for EBI_AD only applies to multiplexed addressing modes D8A24ALE and D16A16ALE)

[2] Applies for both EBI_REn and EBI_NANDREn (figure only shows EBI_REn)

[3] Applies for all polarities (figure only shows active low signals)

[4] Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

[5] The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFRE=0. The leading edge of EBI_REn can be moved to the right by setting HALFRE=1. This decreases the length of t_{WIDTH_REn} and increases the length of t_{OSU_REn} by 1/2 * $t_{HFCLKNODIV}$.

[6] When page mode is used, RDSTRB is replaced by RDPA for page hits.

Table 3.28. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		1000[1]	kHz
t_{LOW}	SCL clock low time	0.5			µs
t_{HIGH}	SCL clock high time	0.26			µs
$t_{SU,DAT}$	SDA set-up time	50			ns
$t_{HD,DAT}$	SDA hold time	8			ns
$t_{SU,STA}$	Repeated START condition set-up time	0.26			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.26			µs
$t_{SU,STO}$	STOP condition set-up time	0.26			µs
t_{BUF}	Bus free time between a STOP and a START condition	0.5			µs

[1] For the minimum HFPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32WG Reference Manual.

3.18 USART SPI

Figure 3.43. SPI Master Timing

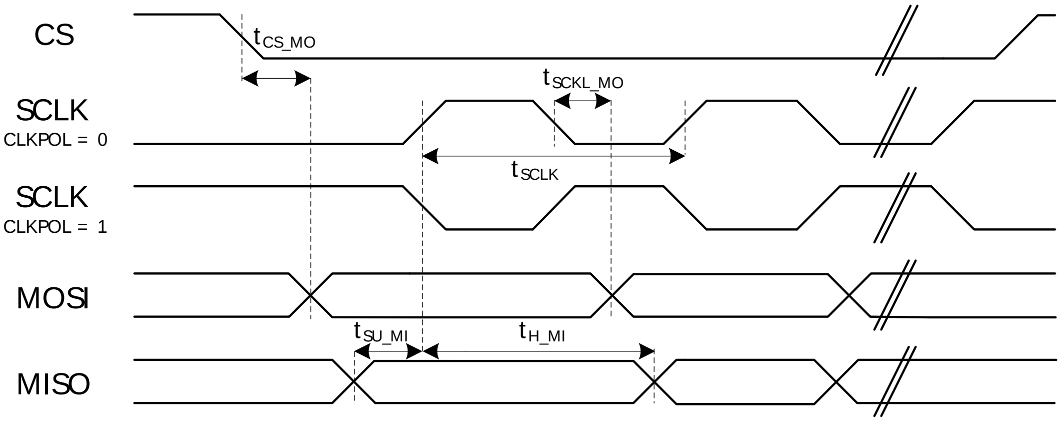


Table 3.29. SPI Master Timing

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_{SCLK} [1] [2]	SCLK period		2 * $t_{HFPERCLK}$			ns
t_{CS_MO} [1] [2]	CS to MOSI		-2.00		2.00	ns
t_{SCLK_MO} [1] [2]	SCLK to MOSI		-1.00		3.00	ns
t_{SU_MI} [1] [2]	MISO setup time	IOVDD = 3.0 V	36.00			ns
t_{H_MI} [1] [2]	MISO hold time		-6.00			ns

[1] Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

[2] Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

BGA112 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
A4	PE9	LCD_SEG5	EBI_AD01 #0/1/2	PCNT2_S1IN #1		
A5	PD10	LCD_SEG29	EBI_CS1 #0/1/2			
A6	PF7	LCD_SEG25	EBI_BL1 #0/1/2	TIM0_CC1 #2	U0_RX #0	
A7	PF5	LCD_SEG3	EBI_REn #0/2	TIM0_CDTI2 #2/5		PRS_CH2 #1
A8	PF4	LCD_SEG2	EBI_WEn #0/2	TIM0_CDTI1 #2/5		PRS_CH1 #1
A9	PE4	LCD_COM0	EBI_A11 #0/1/2		US0_CS #1	
A10	PC14	ACMP1_CH6 DAC0_OUT1ALT #2/ OPAMP_OUT1ALT		TIM0_CDTI1 #1/3 TIM1_CC1 #0 PCNT0_S1IN #0	US0_CS #3 U0_TX #3	LES_CH14 #0
A11	PC15	ACMP1_CH7 DAC0_OUT1ALT #3/ OPAMP_OUT1ALT		TIM0_CDTI2 #1/3 TIM1_CC2 #0	US0_CLK #3 U0_RX #3	LES_CH15 #0 DBG_SWO #1
B1	PA15	LCD_SEG12	EBI_AD08 #0/1/2	TIM3_CC2 #0		
B2	PE13	LCD_SEG9	EBI_AD05 #0/1/2		US0_TX #3 US0_CS #0 I2C0_SCL #6	LES_ALTEX7 #0 ACMP0_O #0 GPIO_EM4WU5
B3	PE11	LCD_SEG7	EBI_AD03 #0/1/2	TIM1_CC1 #1	US0_RX #0	LES_ALTEX5 #0 BOOT_RX
B4	PE8	LCD_SEG4	EBI_AD00 #0/1/2	PCNT2_S0IN #1		PRS_CH3 #1
B5	PD11	LCD_SEG30	EBI_CS2 #0/1/2			
B6	PF8	LCD_SEG26	EBI_WEn #1	TIM0_CC2 #2		ETM_TCLK #1
B7	PF6	LCD_SEG24	EBI_BL0 #0/1/2	TIM0_CC0 #2	U0_TX #0	
B8	PF3	LCD_SEG1	EBI_ALE #0	TIM0_CDTI0 #2/5		PRS_CH0 #1 ETM_TD3 #1
B9	PE5	LCD_COM1	EBI_A12 #0/1/2		US0_CLK #1	
B10	PC12	ACMP1_CH4 DAC0_OUT1ALT #0/ OPAMP_OUT1ALT			U1_TX #0	CMU_CLK0 #1 LES_CH12 #0
B11	PC13	ACMP1_CH5 DAC0_OUT1ALT #1/ OPAMP_OUT1ALT		TIM0_CDTI0 #1/3 TIM1_CC0 #0 TIM1_CC2 #4 PCNT0_S0IN #0	U1_RX #0	LES_CH13 #0
C1	PA1	LCD_SEG14	EBI_AD10 #0/1/2	TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0 PRS_CH1 #0
C2	PA0	LCD_SEG13	EBI_AD09 #0/1/2	TIM0_CC0 #0/1/4	LEU0_RX #4 I2C0_SDA #0	PRS_CH0 #0 GPIO_EM4WU0
C3	PE10	LCD_SEG6	EBI_AD02 #0/1/2	TIM1_CC0 #1	US0_TX #0	BOOT_TX
C4	PD13					ETM_TD1 #1
C5	PD12	LCD_SEG31	EBI_CS3 #0/1/2			
C6	PF9	LCD_SEG27	EBI_REn #1			ETM_TD0 #1
C7	VSS	Ground				
C8	PF2	LCD_SEG0	EBI_ARDY #0/1/2	TIM0_CC2 #5	LEU0_TX #4	ACMP1_O #0 DBG_SWO #0 GPIO_EM4WU4
C9	PE6	LCD_COM2	EBI_A13 #0/1/2		US0_RX #1	
C10	PC10	ACMP1_CH2	EBI_A10 #1/2	TIM2_CC2 #2	US0_RX #2	LES_CH10 #0
C11	PC11	ACMP1_CH3	EBI_ALE #1/2		US0_TX #2	LES_CH11 #0
D1	PA3	LCD_SEG16	EBI_AD12 #0/1/2	TIM0_CDTI0 #0	U0_TX #2	LES_ALTEX2 #0

The BGA112 Package uses SAC105 solderballs.

All EFM32 packages are RoHS compliant and free of Bromine (Br) and Antimony (Sb).

For additional Quality and Environmental information, please see:
http://www.silabs.com/support/quality/pages/default.aspx

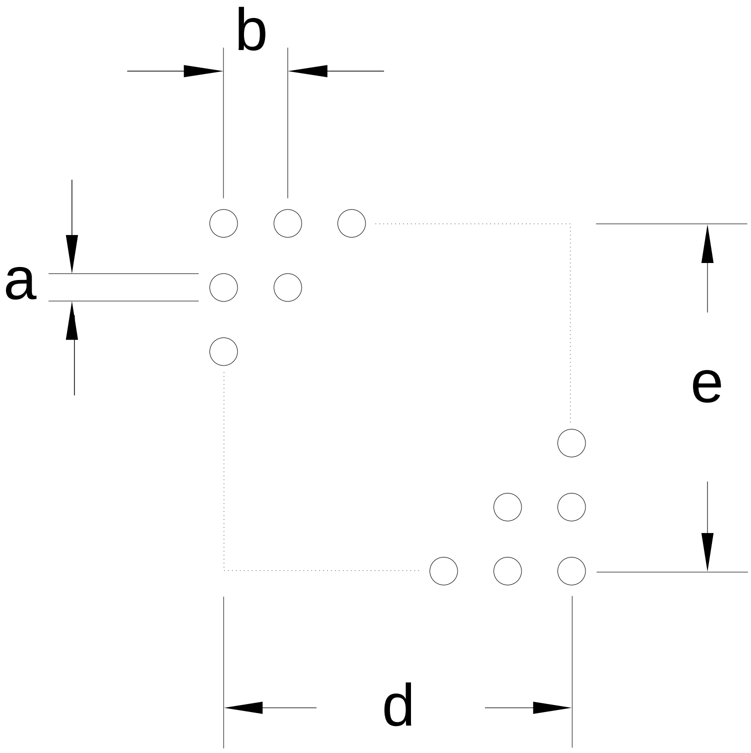


Figure 5.2. BGA112 PCB Solder Mask

Table 5.2. BGA112 PCB Solder Mask Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	0.48
b	0.80
d	8.00
e	8.00

Figure 5.3. BGA112 PCB Stencil Design

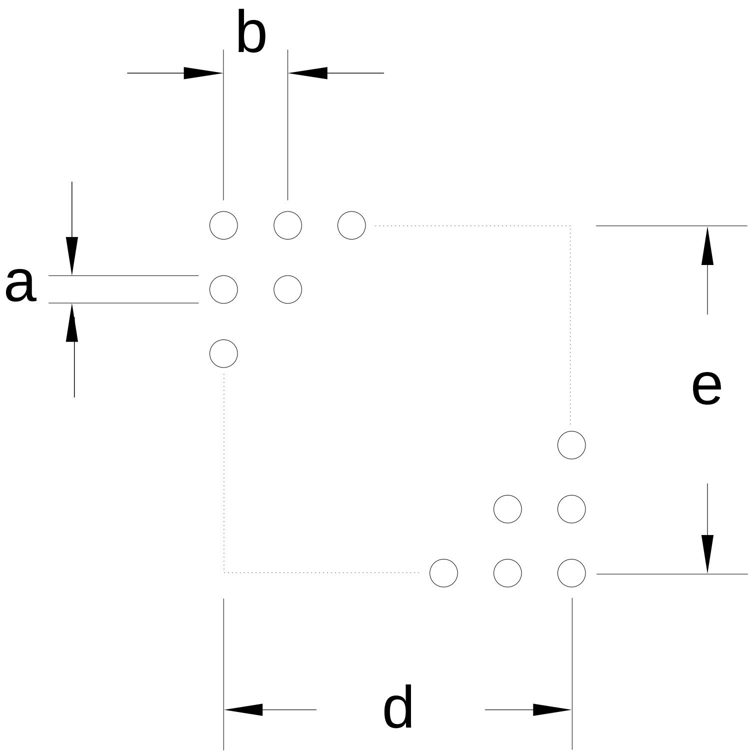


Table 5.3. BGA112 PCB Stencil Design Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	0.33
b	0.80
d	8.00
e	8.00

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.3 (p. 71) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

The packages have a Moisture Sensitivity Level rating of 3, please see the latest IPC/JEDEC J-STD-033 standard for MSL description and level 3 bake conditions.

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ZERO
ARM Cortex-M0+

TINY
ARM Cortex-M3

GECKO
ARM Cortex-M3

LEOPARD
ARM Cortex-M3

GIANT
ARM Cortex-M3

WONDER
ARM Cortex-M4